

High Efficiency Thyristor

$$V_{RRM} = 1200\text{ V}$$

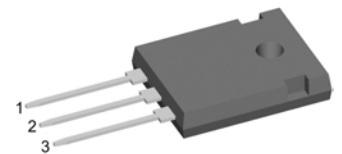
$$I_{TAV} = 30\text{ A}$$

$$V_T = 1,25\text{ V}$$

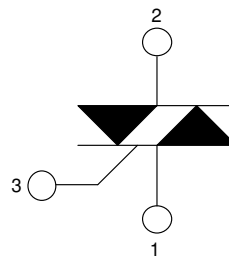
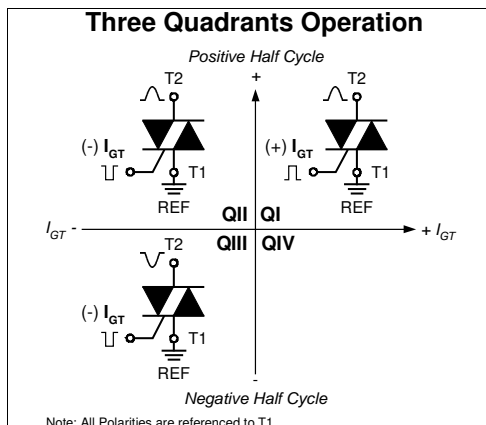
Three Quadrants operation: QI - QIII
 1~ Triac

Part number

CLA60MT1200NHB



Backside: Terminal 2



Features / Advantages:

- Triac for line frequency
- Three Quadrants Operation
 - QI - QIII
- Planar passivated chip
- Long-term stability of blocking currents and voltages

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-247

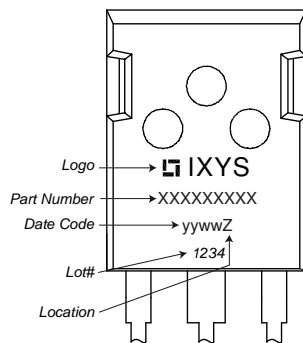
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

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Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
I_{RD}	reverse current, drain current	$V_{R/D} = 1200 V$	$T_{VJ} = 25^{\circ}C$		10	μA	
		$V_{R/D} = 1200 V$	$T_{VJ} = 125^{\circ}C$		2	mA	
V_T	forward voltage drop	$I_T = 30 A$	$T_{VJ} = 25^{\circ}C$		1,28	V	
		$I_T = 60 A$			1,56	V	
		$I_T = 30 A$	$T_{VJ} = 125^{\circ}C$		1,25	V	
		$I_T = 60 A$			1,61	V	
I_{TAV}	average forward current	$T_C = 120^{\circ}C$	$T_{VJ} = 150^{\circ}C$		30	A	
I_{RMS}	RMS forward current per phase	180° sine			66	A	
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0,86	V	
r_T	slope resistance				12,5	m Ω	
R_{thJC}	thermal resistance junction to case				0,55	K/W	
R_{thCH}	thermal resistance case to heatsink			0,25		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		230	W	
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		380	A	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		410	A	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		325	A	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		350	A	
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		720	A ² s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		700	A ² s	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		530	A ² s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		510	A ² s	
C_J	junction capacitance	$V_R = 400V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		25	pF	
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 150^{\circ}C$		10	W	
		$t_p = 300 \mu s$			5	W	
P_{GAV}	average gate power dissipation				0,5	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}C; f = 50 \text{ Hz}$ repetitive, $I_T = 90 A$			150	A/ μs	
		$t_p = 200 \mu s; di_G/dt = 0,3 A/\mu s;$ $I_G = 0,3A; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 30 A$			500	A/ μs	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 150^{\circ}C$		500	V/ μs	
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1,7	V	
			$T_{VJ} = -40^{\circ}C$		1,9	V	
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		± 60	mA	
			$T_{VJ} = -40^{\circ}C$		± 80	mA	
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		0,2	V	
I_{GD}	gate non-trigger current				± 1	mA	
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		90	mA	
		$I_G = 0,3A; di_G/dt = 0,3 A/\mu s$					
I_H	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		60	mA	
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs	
		$I_G = 0,3A; di_G/dt = 0,3 A/\mu s$					
t_q	turn-off time	$V_R = 100 V; I_T = 30A; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s; dv/dt = 20 V/\mu s; t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		150	μs	

Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			70	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				6		g
M_D	mounting torque		0,8		1,2	Nm
F_C	mounting force with clip		20		120	N

Product Marking

Part description

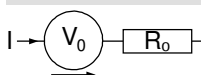
C = Thyristor (SCR)
 L = High Efficiency Thyristor
 A = (up to 1200V)
 60 = Current Rating [A]
 MT = 1~ Triac
 1200 = Reverse Voltage [V]
 N = Three Quadrants operation: QI - QIII
 HB = TO-247AD (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLA60MT1200NHB	CLA60MT1200NHB	Tube	30	512073

Similar Part	Package	Voltage class
CLA60MT1200NHR	ISO247 (3)	1200
CLA60MT1200NTZ	TO-268AA (D3Pak) (2HV)	1200

Equivalent Circuits for Simulation

* on die level

 $T_{VJ} = 150^{\circ}\text{C}$

Thyristor

$V_{0 \max}$	threshold voltage	0,86	V
$R_{0 \max}$	slope resistance *	10	mΩ

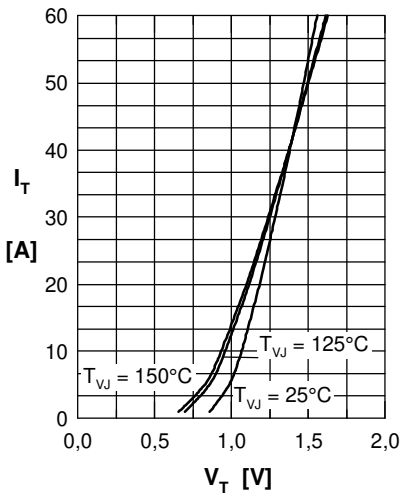
Thyristor


Fig. 1 Forward characteristics

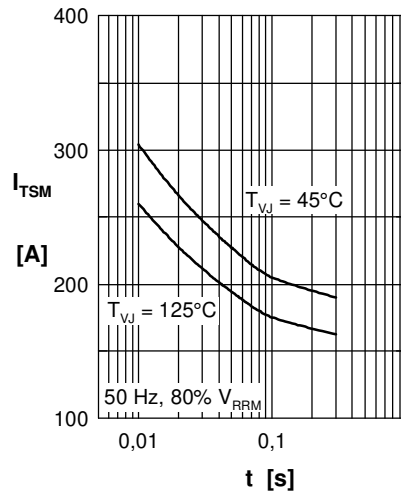
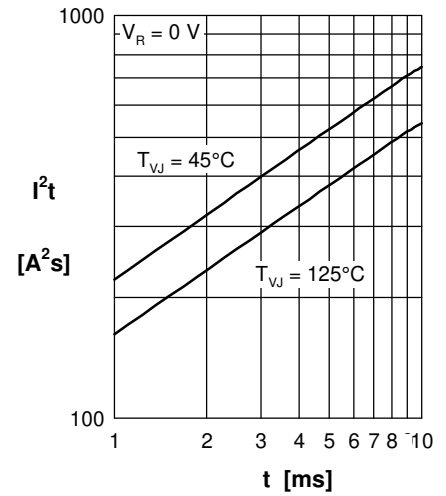
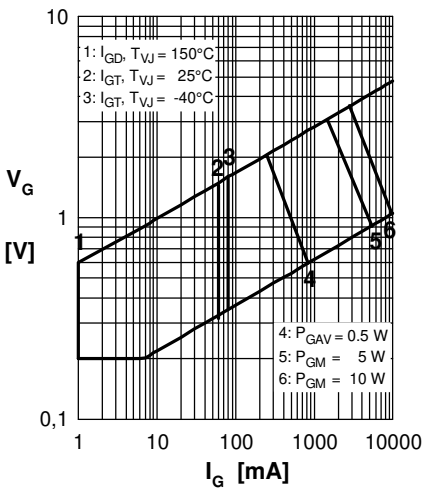

 Fig. 2 Surge overload current
 I_{TSM} : crest value, t : duration

 Fig. 3 I^2t versus time (1-10 s)


Fig. 4 Gate voltage & gate current

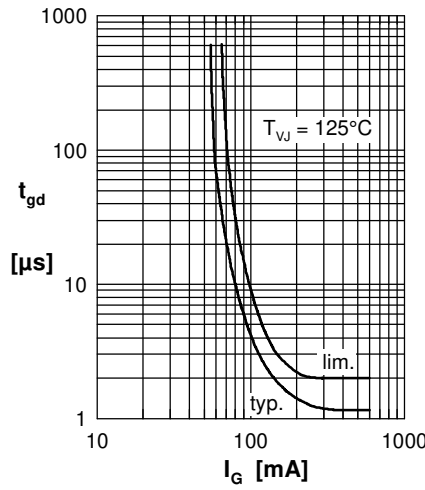
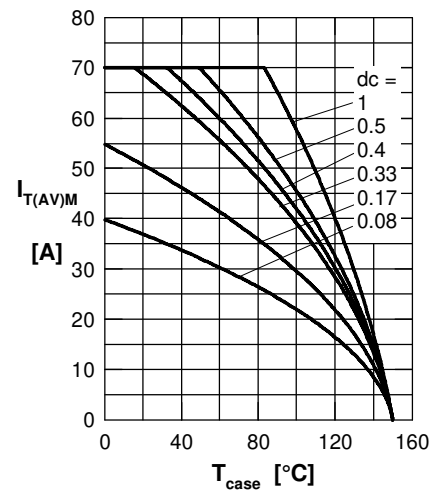

 Fig. 5 Gate controlled delay time t_{gd}


Fig. 6 Max. forward current at case temperature

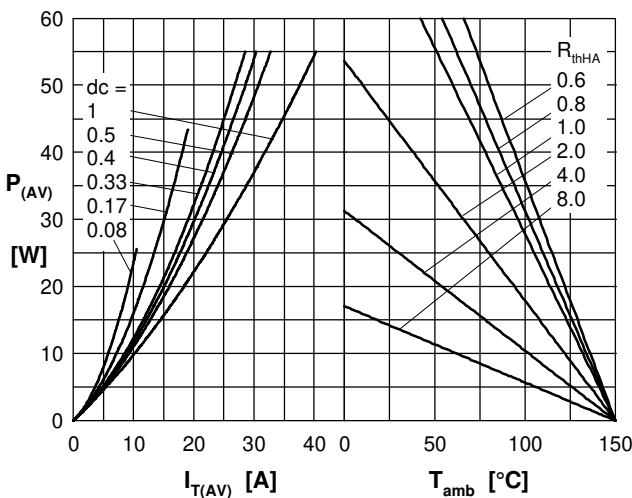
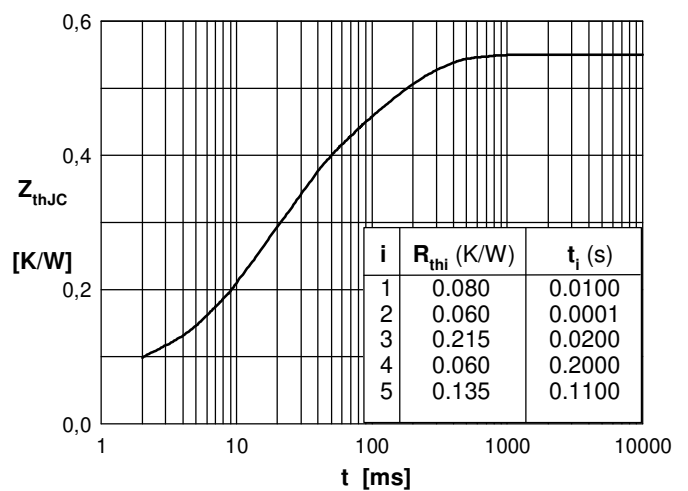

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 7 Transient thermal impedance junction to case